Ap	plication No.	Applicant(s)
10	/720,094	BITO, YASUNORI
Notice of Allowability Exa	aminer	Art Unit
	omas L. Dickey	2826
The MAILING DATE of this communication appears I claims being allowable, PROSECUTION ON THE MERITS IS (ORe rewith (or previously mailed), a Notice of Allowance (PTOL-85) or of OTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHT the Office or upon petition by the applicant. See 37 CFR 1.313 and This communication is responsive to drawings and amendment.	REMAINS) CLOSED in ther appropriate community. This application is a MPEP 1308.	n this application. If not included unication will be mailed in due course. THIS
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. ☑ The allowed claim(s) is/are <u>1-8,10-13 and 15-18</u> .		
. Acknowledgment is made of a claim for foreign priority under	35 U.S.C. § 119(a)-(d)	or (f).
 a)	an received	
Certified copies of the priority documents have been copies of the priority documents have been copies.		n No
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International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of th noted below. Failure to timely comply will result in ABANDONMENT THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	is communication to file Γof this application.	a reply complying with the requirements
. A SUBSTITUTE OATH OR DECLARATION must be submitted INFORMAL PATENT APPLICATION (PTO-152) which gives re	. Note the attached EXA ason(s) why the oath or	AMINER'S AMENDMENT or NOTICE OF declaration is deficient.
. CORRECTED DRAWINGS (as "replacement sheets") must be	submitted.	
(a) I including changes required by the Notice of Draftsperson's		v (PTO-948) attached
1) hereto or 2) to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Am Paper No./Mail Date		
Identifying indicia such as the application number (see 37 CFR 1.84(c each sheet. Replacement sheet(s) should be labeled as such in the he)) should be written on the eader according to 37 CF	ne drawings in the front (not the back) of R 1.121(d).
. DEPOSIT OF and/or INFORMATION about the deposit o attached Examiner's comment regarding REQUIREMENT FOR	f BIOLOGICAL MATE THE DEPOSIT OF BIO	ERIAL must be submitted. Note the DLOGICAL MATERIAL.
ttachment(s) Notice of References Cited (PTO-892)	5. 🗀 Notice of Int	formal Patent Application (PTO-152)
☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	<u> </u>	ummary (PTO-413),
	Paper No./	Mail Date ^ Amendment/Comment
Paper No./Mail Date 10/17/2005	_	
	8. IXI Examiner's	Statement of Reasons for Allowance
☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material		

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EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

The application has been amended as follows:

IN THE CLAIMS:

Cancel claims 19-35.

DRAWINGS

2. The proposed drawing correction and/or the proposed substitute sheets of drawings, filed on 02/02/2006 have been approved.

REASONS FOR ALLOWANCE

3. The following is an examiner's statement of reasons for allowance:

Claims 1-8,10-13 and 15-18 are allowed over the references of record because none of these references disclosed or can be combined to yield the claimed invention such as a heterojunction field effect type semiconductor device, comprising a GaAs substrate; a channel layer formed over said GaAs substrate; a first semiconductor layer including no aluminum formed over said channel layer; a cap layer of a first conductivity

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type formed on said first semiconductor layer, said cap layer creating a first recess on said first semiconductor layer; first and second ohmic electrodes formed on said cap layer, respectively; a second semiconductor layer of second conductivity type formed on said first semiconductor layer within said first recess, said second semiconductor layer being isolated from said cap layer; a gate electrode formed on said second semiconductor layer; and a third semiconductor layer interposed between said first semiconductor layer and said cap layer and having a second recess, said second semiconductor layer passing through the second recess of said third semiconductor layer to reach said first semiconductor layer, said third semiconductor layer comprising a GaAs layer formed on an AlGaAs layer, as recited in claim 1.

As was noted in the Paper mailed 6/16/05, Kato et al. discloses a heterojunction field effect type semiconductor device with all the limitations of claim 1 except Kato et al.'s two part GaAs/AlGaAs third semiconductor layer has a first AlGaAs part 511 formed on a second GaAs part 510. Claim 1 requires the second GaAs part of the third layer to be formed on the first AlGaAs part.

4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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Conclusion

1. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thomas L Dickey whose telephone number is 571-272-1913. The examiner can normally be reached on Monday-Thursday 8-6.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

> Thomas L. Dickey Patent Examiner Art Unit 2826 02/06